

BD675, BD675A, BD677, BD677A, BD679, BD679A, BD681

BD681 is a Preferred Device

Plastic Medium-Power Silicon NPN Darlington

This series of plastic, medium-power silicon NPN Darlington transistors can be used as output devices in complementary general-purpose amplifier applications.

Features

- High DC Current Gain:

$$h_{FE} = 750 \text{ (Min) @ } I_C$$

$$= 1.5 \text{ and } 2.0 \text{ Adc}$$
- Monolithic Construction
- BD675, 675A, 677, 677A, 679, 679A, 681 are complementary with BD676, 676A, 678, 678A, 680, 680A, 682
- BD677, 677A, 679, 679A are equivalent to MJE 800, 801, 802, 803
- Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage BD675, A BD677, A BD679, A BD681	V_{CEO}	45 60 80 100	Vdc
Collector-Base Voltage BD675, A BD677, A BD679, A BD681	V_{CBO}	45 60 80 100	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current	I_C	4.0	Adc
Base Current	I_B	1.0	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	40 0.32	W W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	θ_{JC}	3.13	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

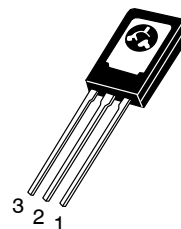
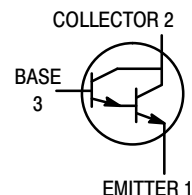
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



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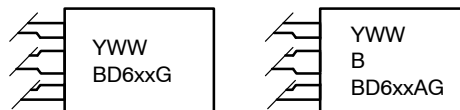
<http://onsemi.com>

**4.0 AMPERES
POWER TRANSISTORS
NPN SILICON
60, 80, 100 VOLTS, 40 WATTS**



TO-225AA
CASE 77
STYLE 1

MARKING DIAGRAMS



BD6xx = Device Code
 x = 75, 77, 79, 81
 Y = Year
 WW = Work Week
 G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

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ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage, (Note 1) ($I_C = 50\text{ mAdc}$, $I_B = 0$)	BD675, 675A BD677, 677A BD679, 679A BD681	BV_{CEO}	45 60 80 100	– – – –	Vdc
Collector Cutoff Current ($V_{CE} = \text{Half Rated } BV_{CEO}$, $I_B = 0$)		I_{CEO}	–	500	μAdc
Collector Cutoff Current ($V_{CB} = \text{Rated } BV_{CEO}$, $I_E = 0$) ($V_{CB} = \text{Rated } BV_{CEO}$, $I_E = 0$, $T_C = 100^\circ\text{C}$)		I_{CBO}	– –	0.2 2.0	mAdc
Emitter Cutoff Current ($V_{BE} = 5.0\text{ Vdc}$, $I_C = 0$)		I_{EBO}	–	2.0	mAdc

ON CHARACTERISTICS

DC Current Gain, (Note 1) ($I_C = 1.5\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$) ($I_C = 2.0\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$)	BD675, 677, 679, 681 BD675A, 677A, 679A	h_{FE}	750 750	– –	–
Collector-Emitter Saturation Voltage, (Note 1) ($I_C = 1.5\text{ Adc}$, $I_B = 30\text{ mAdc}$) ($I_C = 2.0\text{ Adc}$, $I_B = 40\text{ mAdc}$)	BD677, 679, 681 BD675A, 677A, 679A	$V_{CE(sat)}$	– –	2.5 2.8	Vdc
Base-Emitter On Voltage, (Note 1) ($I_C = 1.5\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$) ($I_C = 2.0\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$)	BD677, 679, 681 BD675A, 677A, 679A	$V_{BE(on)}$	– –	2.5 2.5	Vdc

DYNAMIC CHARACTERISTICS

Small Signal Current Gain ($I_C = 1.5\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$, $f = 1.0\text{ MHz}$)	h_{fe}	1.0	–	–
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1. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

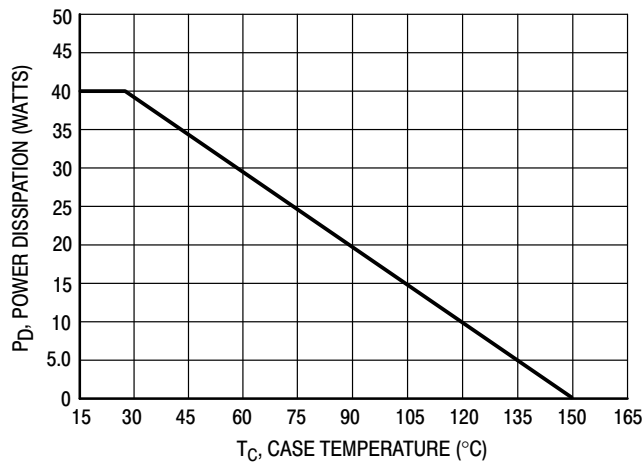


Figure 1. Power Temperature Derating

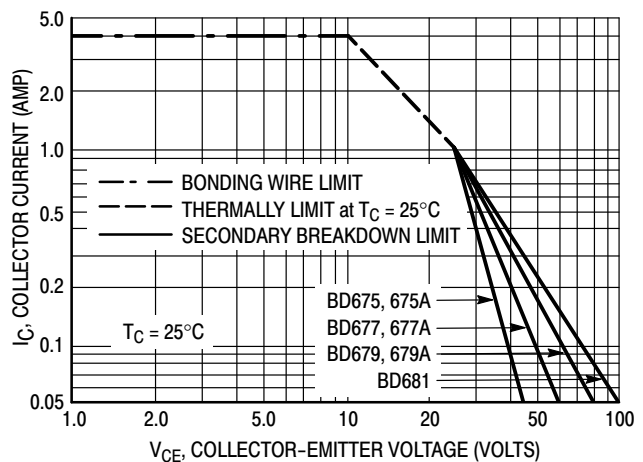


Figure 2. DC Safe Operating Area

There are two limitations on the power handling ability of a transistor average junction temperature and secondary breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; e.g., the transistor must not be subjected to greater dissipation than the curves indicate.

At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by secondary breakdown.

BD675, BD675A, BD677, BD677A, BD679, BD679A, BD681

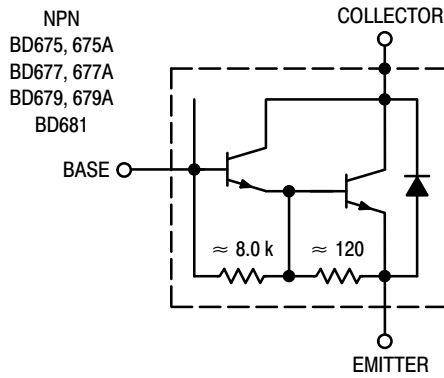


Figure 3. Darlington Circuit Schematic

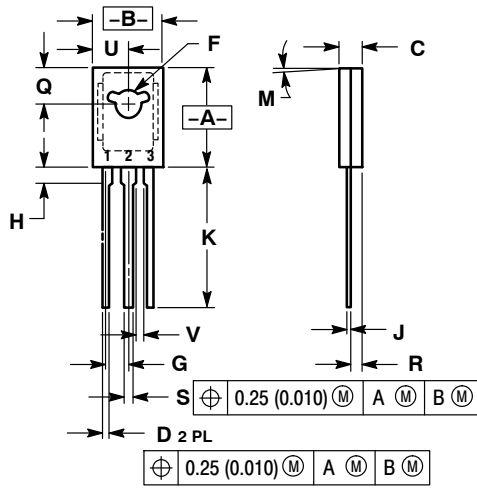
ORDERING INFORMATION

Device	Package	Shipping
BD675	TO-225AA	500 Units / Box
BD675G	TO-225AA (Pb-Free)	500 Units / Box
BD675A	TO-225AA	500 Units / Box
BD675AG	TO-225AA (Pb-Free)	500 Units / Box
BD677	TO-225AA	500 Units / Box
BD677G	TO-225AA (Pb-Free)	500 Units / Box
BD677A	TO-225AA	500 Units / Box
BD677AG	TO-225AA (Pb-Free)	500 Units / Box
BD679	TO-225AA	500 Units / Box
BD679G	TO-225AA (Pb-Free)	500 Units / Box
BD679A	TO-225AA	500 Units / Box
BD679AG	TO-225AA (Pb-Free)	500 Units / Box
BD681	TO-225AA	500 Units / Box
BD681G	TO-225AA (Pb-Free)	500 Units / Box

BD675, BD675A, BD677, BD677A, BD679, BD679A, BD681

PACKAGE DIMENSIONS

TO-225AA
CASE 77-09
ISSUE Z



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 077-01 THRU -08 OBSOLETE, NEW STANDARD 077-09.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.065	1.15	1.65
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	---	1.02	---

STYLE 1:

1. EMITTER
2. COLLECTOR
3. BASE

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Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

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В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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